

## APPENDIX

## Changes to Claims:

Claims 15 and 16 are added.

The following are marked-up versions of the amended claims:

1. (Amended) A semiconductor device, comprising:  
~~\_\_\_\_\_ a silicon substrate and~~  
a metal-oxide-semiconductor field-effect transistor ~~formed on said silicon~~  
~~substrate,~~  
~~\_\_\_\_\_ wherein a gate electrode of said transistor comprises a germanium film that~~  
includes:  
\_\_\_\_\_ a gate insulation film and a gate electrode on the gate insulation film,  
the gate electrode including a germanium film on the gate insulation film.
7. (Amended) A semiconductor device, comprising:  
an n-channel metal-oxide-semiconductor field-effect transistor; and  
a p-channel metal-oxide-semiconductor field-effect transistor,  
~~wherein a gate electrode of each of said transistors comprises any one of a~~  
~~single-crystalline germanium film, a polycrystalline germanium film or an amorphous~~  
~~germanium film in which p-type impurities are doped~~at least one of the n-channel metal-  
oxide-semiconductor field-effect transistor and the p-channel metal-oxide-semiconductor  
field-effect transistor including:  
\_\_\_\_\_ a gate insulation film and a gate electrode on the gate insulation film,  
the gate electrode including a germanium film on the gate insulation film.